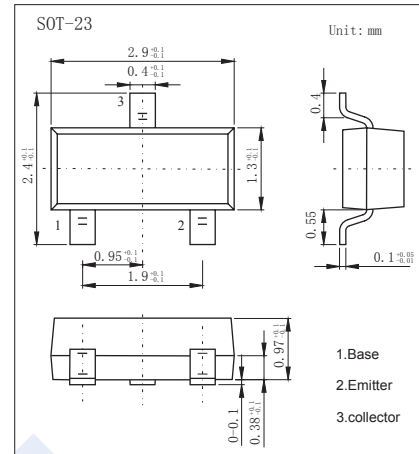


NPN Transistors

2SC4702

■ Features

- Collector Current Capability $I_c=50\text{mA}$
- Collector Emitter Voltage $V_{CE0}=300\text{V}$



■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CB0}	300	V
Collector - Emitter Voltage	V_{CE0}	300	
Emitter - Base Voltage	V_{EB0}	5	
Collector Current - Continuous	I_c	50	mA
Collector Power Dissipation	P_c	150	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55 to 150	

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CB0}	$I_c = 100 \mu\text{A}$, $I_E = 0$	300			V
Collector- emitter breakdown voltage	V_{CE0}	$I_c = 1 \text{ mA}$, $I_B = 0$	300			
Emitter - base breakdown voltage	V_{EB0}	$I_E = 100 \mu\text{A}$, $I_C = 0$	5			
Collector-base cut-off current	I_{CBO}	$V_{CB} = 250 \text{ V}$, $I_E = 0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = 5 \text{ V}$, $I_C = 0$			0.1	μA
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_c = 30 \text{ mA}$, $I_B = 3 \text{ mA}$			0.5	V
Base - emitter saturation voltage	$V_{BE(sat)}$	$I_c = 30 \text{ mA}$, $I_B = 3 \text{ mA}$			1.2	
DC current gain	h_{FE}	$V_{CE} = 6 \text{ V}$, $I_c = 2 \text{ mA}$	60		150	
Collector output capacitance	C_{ob}	$V_{CB} = 10 \text{ V}$, $I_E = 0$, $f = 1 \text{ MHz}$		1.5		pF
Transition frequency	f_T	$V_{CE} = 6 \text{ V}$, $I_c = 5 \text{ mA}$		80		MHz

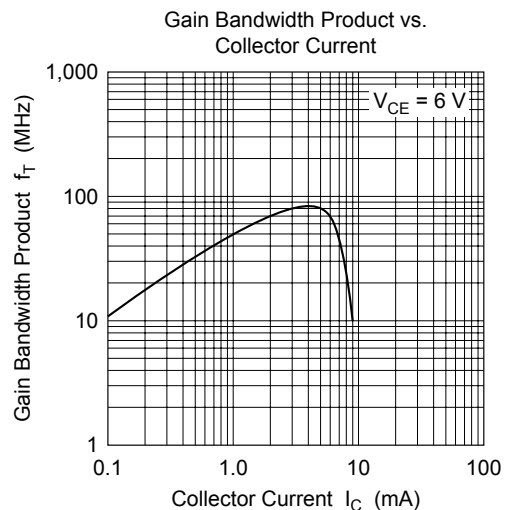
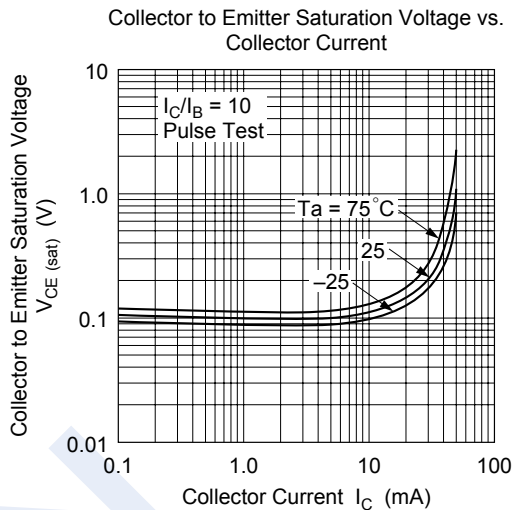
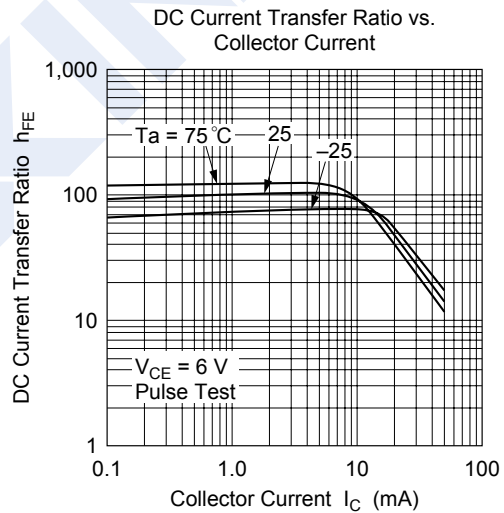
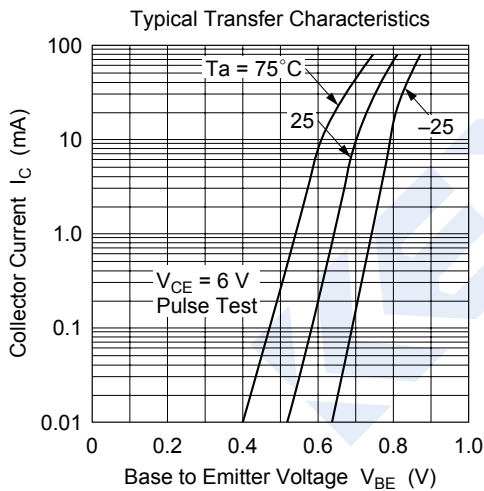
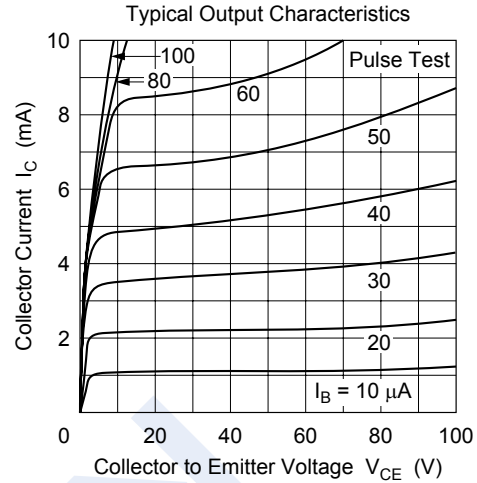
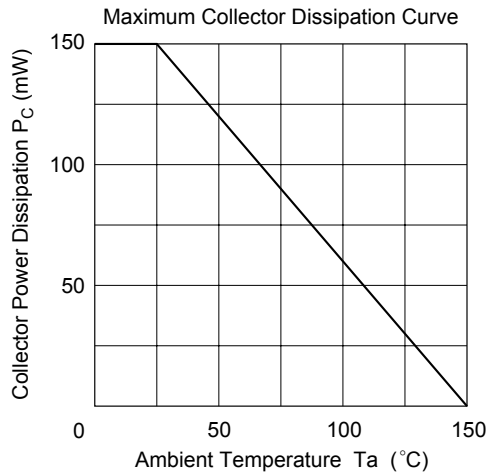
■ Marking

Marking	XV*
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■ Typical Characteristics



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■ Typical Characteristics

